

Supporting Information

Low-temperature vapor reduction of graphene oxide electrodes for vertical organic field-effect transistors

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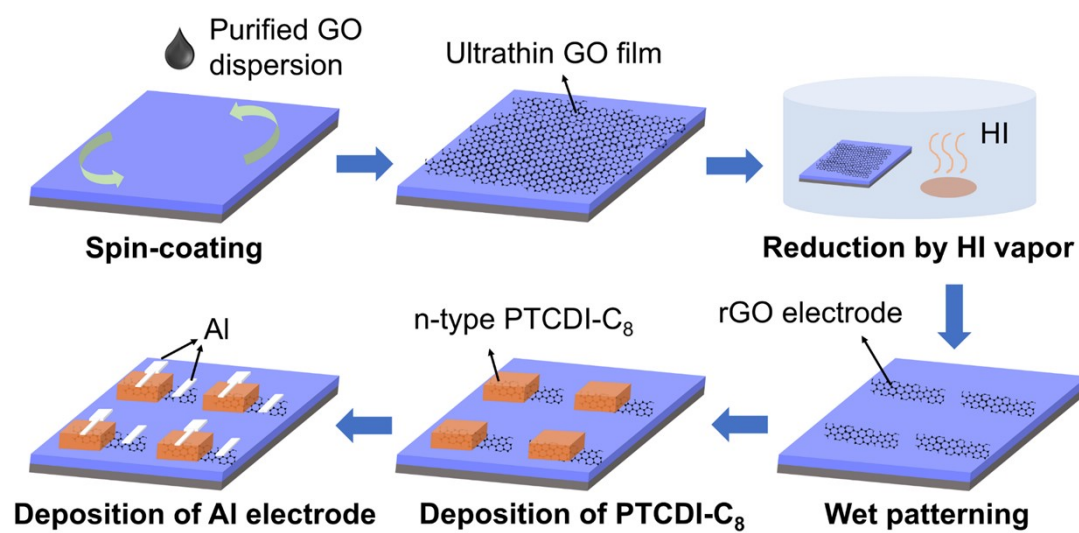


Figure S1. Schematic of the device fabrication process.

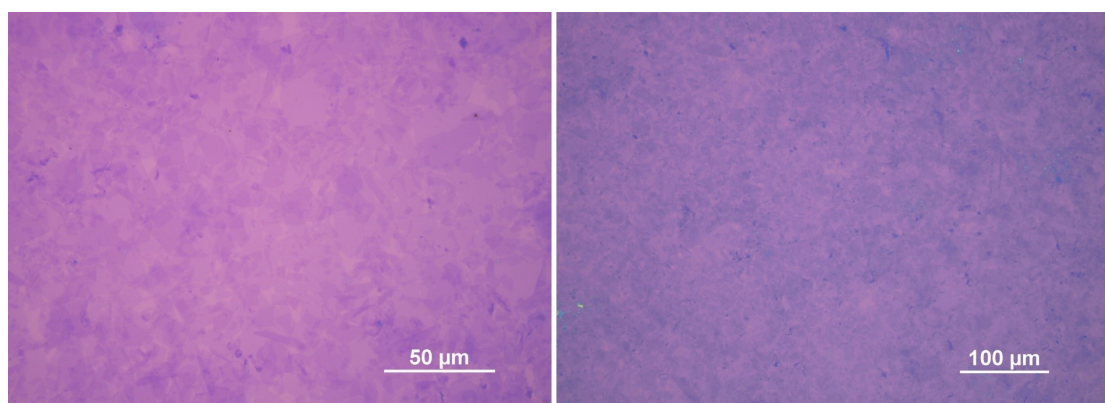


Figure S2. Optical images of the rGO films.

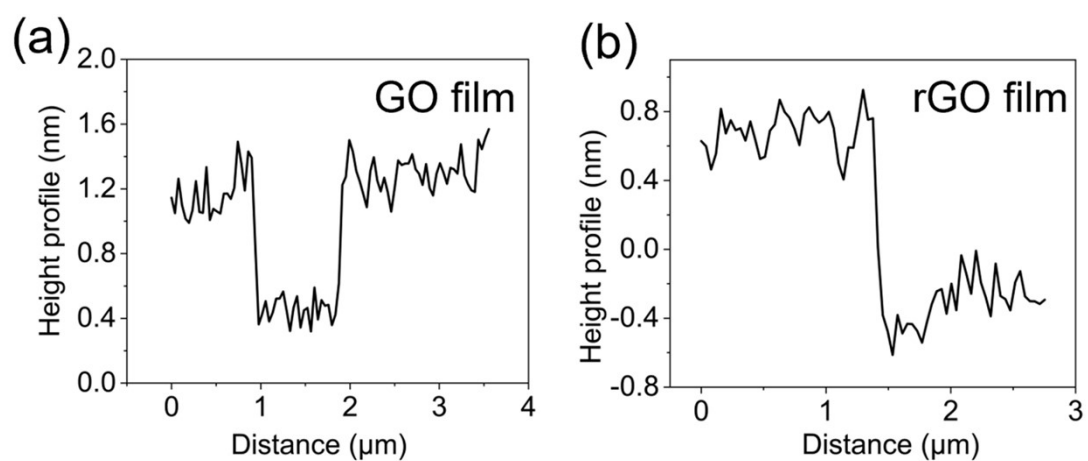


Figure S3. Height profile of the (a) spin-coated GO and (b) rGO film.

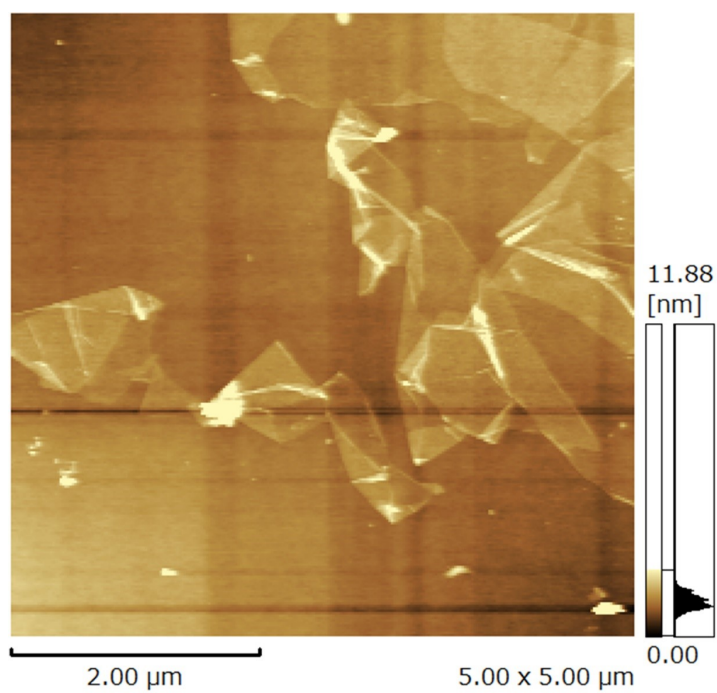


Figure S4. AFM image of the rGO film reduced by dipping in HI solution.

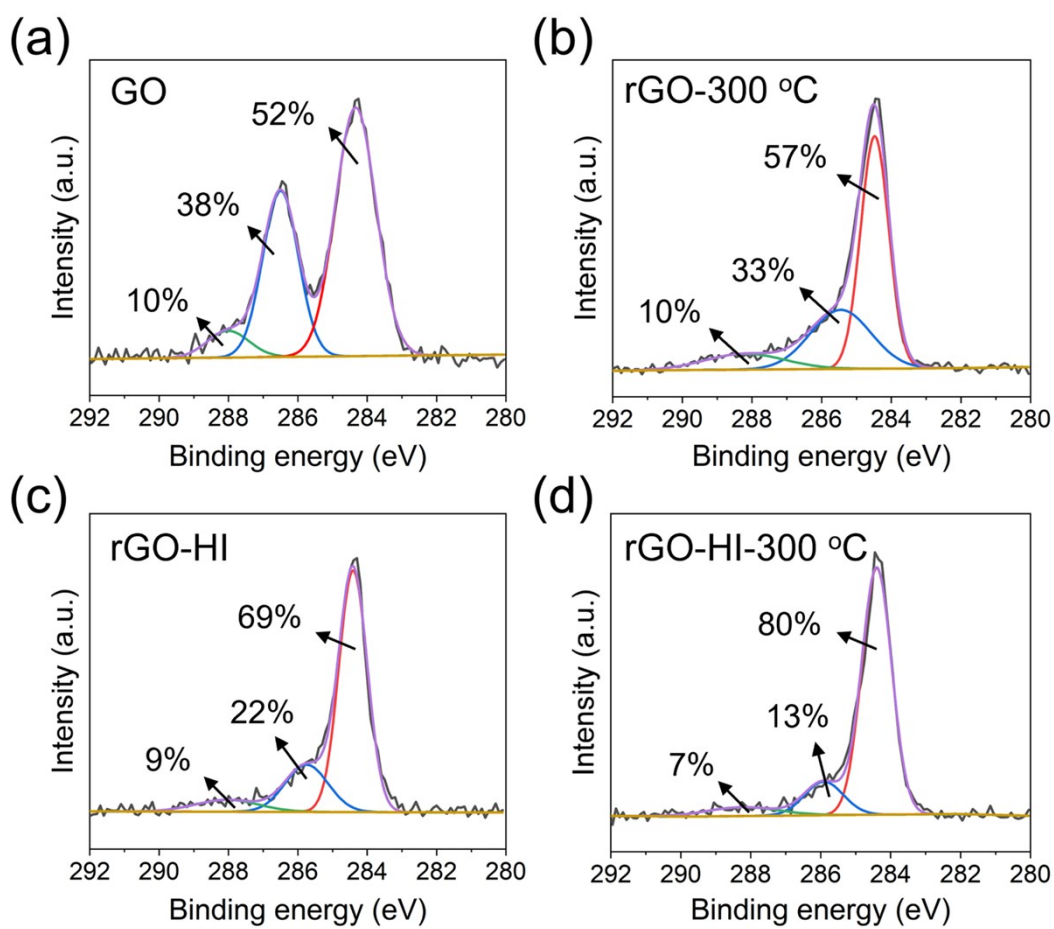


Figure S5. C1s XPS spectra of the (a) GO, (b) rGO-300 °C, (c)rGO-HI and (d) rGO-HI-300 °C, respectively.

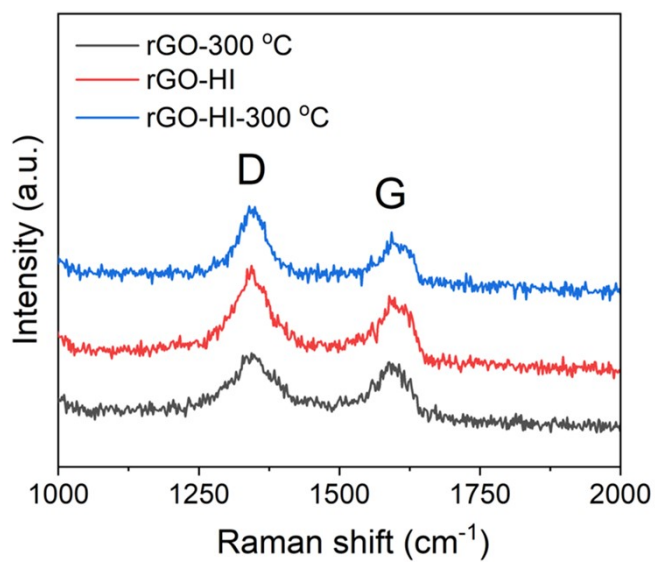


Figure S6. Raman spectra of the rGO-300 °C, rGO-HI, and rGO-HI-300 °C respectively.